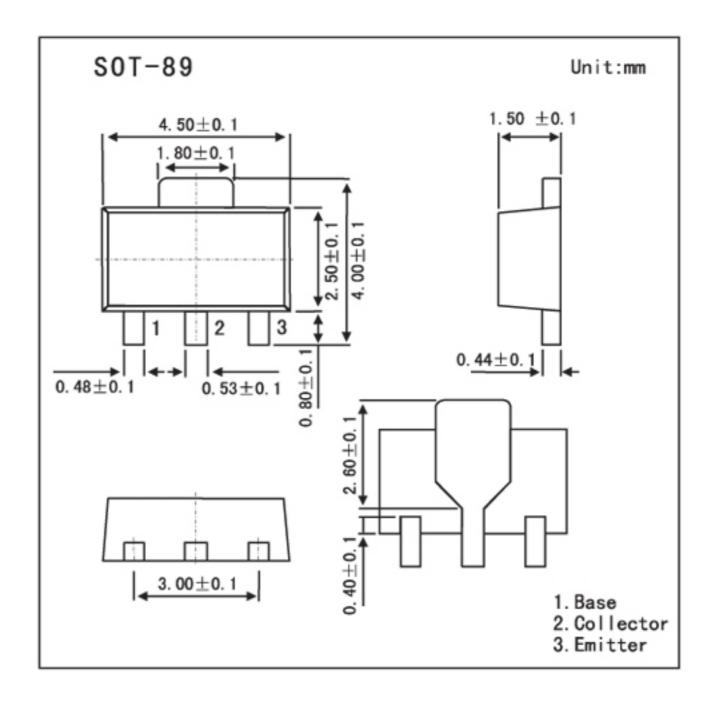


2SD1006

Features

High collector to emitter voltage: VCEO>100V.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	Vсво	100	V	
Collector-emitter voltage	VCEO	100	V	
Emitter-base voltage	Vево	5	V	
Collector current	Ic	0.7	А	
Collector current (pulse) *	IC(pu)	1.2	А	
Collector I power dissipation	Pc	2	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

^{*.} PW≤10ms,duty cycle≤50%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Base-emitter voltage *	VBE	Vce =10V , Ic = 10mA	550	620	650	mV
Collector cutoff current	Ісво	VCB = 100V, IE=0			100	nA
Emitter cutoff current	ІЕВО	VEB = 5V, IC=0			100	nA
DC current gain *	hFE	Vce =1V , Ic = 5.0mA	45	200		
		Vce =1V , Ic = 100mA	90	200	400	
Collector-emitter saturation voltage *	VCE(sat)	Ic = 500mA , IB = 50mA		0.3	0.6	V
Base-emitter saturation voltage *	VBE(sat)	Ic = 500mA , IB = 50mA		0.9	1.5	٧
Output capacitance	Cob	Vсв = 10V , IE = 0 , f = 1.0MHz		10		pF
Transition product	fT	Vce = 10V , IE = -10mA		90		MHz

^{*.} PW≤350µs,duty cycle≤2%

hFE Classification

Marking	НМ	HL	HK
hFE	90~180	135~270	200~400

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